
2SD667, 2SD667A

Silicon NPN Epitaxial

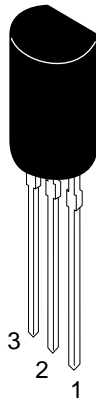
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Application

- Low frequency power amplifier
- Complementary pair with 2SB647/A

Outline

TO-92MOD



1. Emitter
2. Collector
3. Base

2SD667, 2SD667A

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	2SD667	2SD667A	Unit
Collector to base voltage	V_{CBO}	120	120	V
Collector to emitter voltage	V_{CEO}	80	100	V
Emitter to base voltage	V_{EBO}	5	5	V
Collector current	I_C	1	1	A
Collector peak current	$i_{C(peak)}$	2	2	A
Collector power dissipation	P_C	0.9	0.9	W
Junction temperature	T_j	150	150	°C
Storage temperature	T_{stg}	-55 to +150	-50 to +150	°C

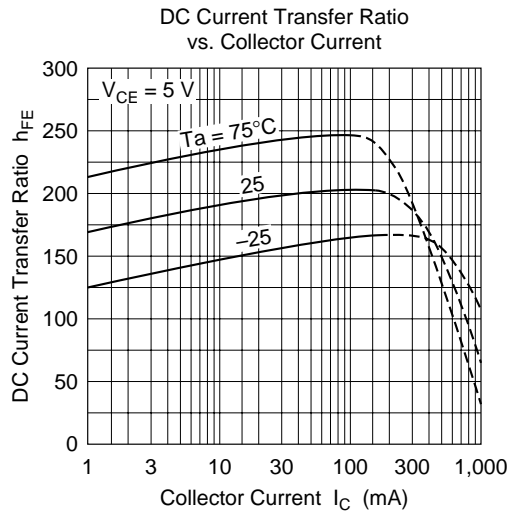
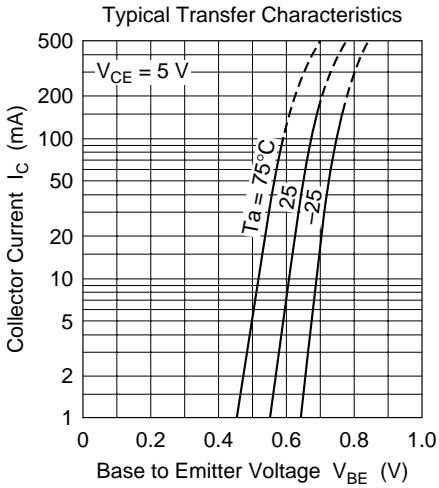
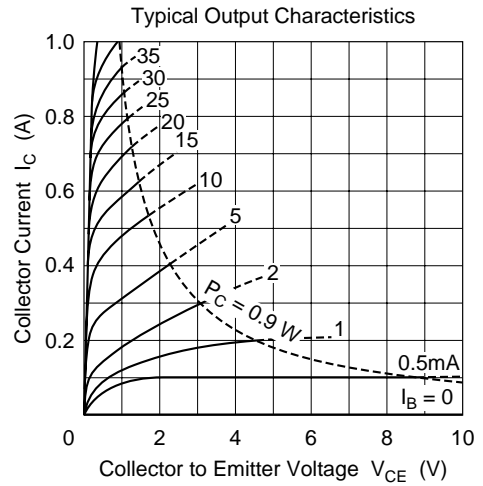
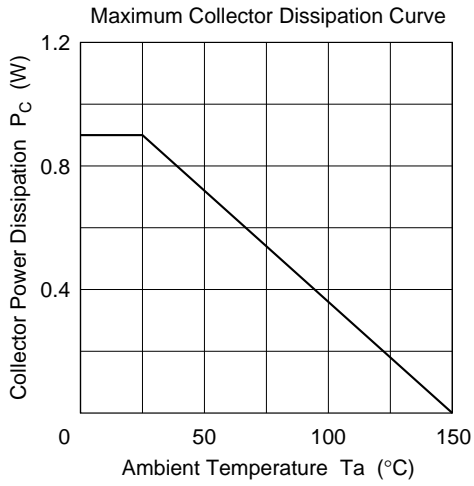
Electrical Characteristics (Ta = 25°C)

Item	Symbol	2SD667			2SD667A			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	120	—	—	120	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	80	—	—	100	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	5	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	10	—	—	10	μA	$V_{CB} = 100 \text{ V}, I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	320	60	—	200		$V_{CE} = 5 \text{ V}, I_C = 150 \text{ mA}^{*2}$
	h_{FE2}	30	—	—	30	—	—		$V_{CE} = 5 \text{ V}, I_C = 500 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1	—	—	1	V	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}^{*2}$
Base to emitter voltage	V_{BE}	—	—	1.5	—	—	1.5	V	$V_{CE} = 5 \text{ V}, I_C = 150 \text{ mA}^{*2}$
Gain bandwidth product	f_T	—	140	—	—	140	—	MHz	$V_{CE} = 5 \text{ V}, I_C = 150 \text{ mA}^{*2}$
Collector output capacitance	C_{ob}	—	12	—	—	12	—	pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$

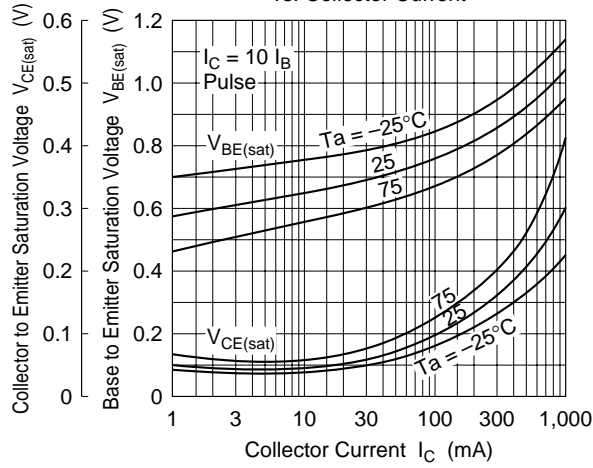
Notes: 1. The 2SD667 and 2SD667A are grouped by h_{FE1} as follows.

2. Pulse test

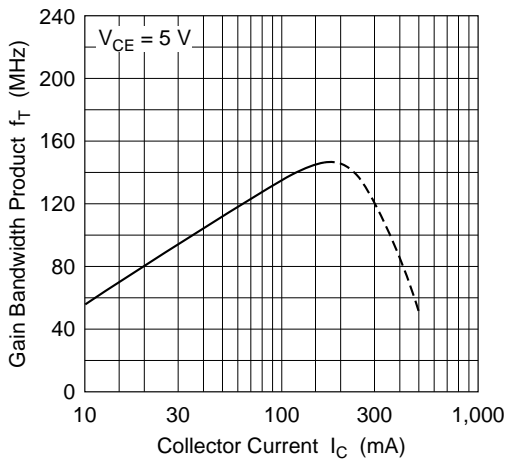
	B	C	D
2SD667	60 to 120	100 to 200	160 to 320
2SD667A	60 to 120	100 to 200	



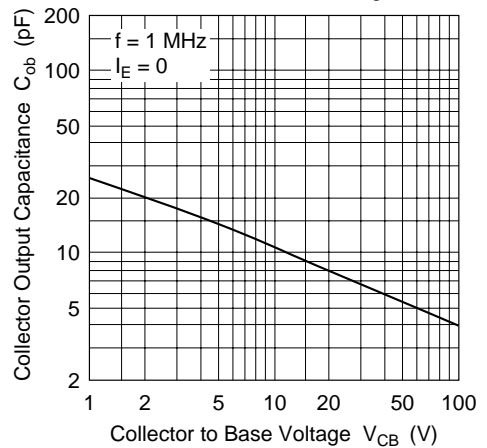
Saturation Voltage vs. Collector Current

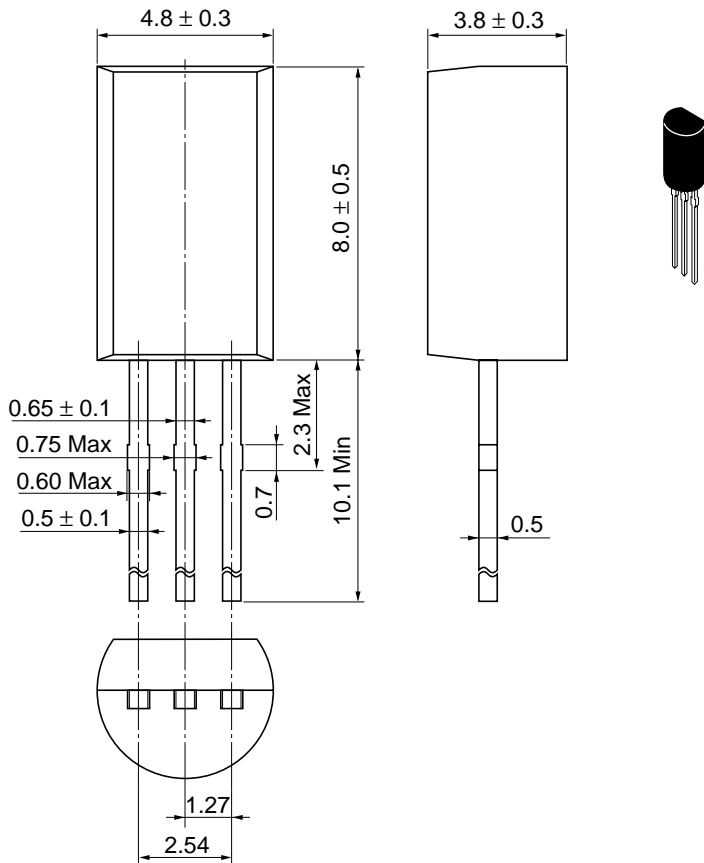


Gain Bandwidth Product vs. Collector Current



Collector Output Capacitance vs. Collector to Base Voltage





Hitachi Code	TO-92 Mod
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.35 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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